



Features and Benefits

- Exceptional reliability
- Small fully-molded SIP package with heatsink mounting for high thermal dissipation and long life
- Operating junction temperature to 150°C
- ${\color{red} \bullet} \ V_{DRM} \ of \ 700 \ or \ 800 \ V$
- 15.7 A_{RMS} on-state current
- 7 mA typical gate trigger current
- Uniform switching
- UL Recognized Component (File No.: E118037) (suffix I)



Not to scale

Package: 3-pin SIP (TO-220F)



Description

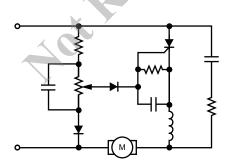
This Sanken reverse blocking triode thyristor is designed for AC power control, providing reliable, uniform switching for half-cycle AC applications.

In comparison with other products on the market, the TFA10x series provides increased isolation voltage (1800 VAC_{RMS}), guaranteed for up to 1 minute. In addition, commutation dv/dt is improved.

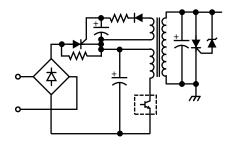
Applications

- Motor control for small tools
- Temperature control, light dimmers, electric blankets
- General use switching mode power supplies (SMPS)

Typical Applications



Single-phase motor control (for example, electric tool)



In-rush current control (for example, SMPS)

Reverse Blocking Triode Thyristor

Selection Guide

Part Number	V _{DRM} (V)	UL-Recognized Component	Package	Packing
TFA107(I)	700	Yes		
TFA107S	700	_	3-pin fully molded SIP with	EO niceses nor tubo
TFA108(I)	800	Yes	heatsink mount	50 pieces per tube
TFA108S	800	_		

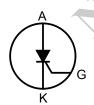
Absolute Maximum Ratings

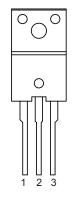
Characteristic	Symbol		Notes	Rating	Units
Peak Repetitive Off-State Voltage	V_{DRM}	TFA107x	T = 40°C to 450°C D = 410	700	V
		TFA108x	$T_J = -40$ °C to 150°C, $R_{GREF} = 1 \text{ k}\Omega$	800	V
Isolation Voltage	V _{ISO}	AC RMS applied for 1 minute between lead and case		1800	V
Average On-State Current	I _{T(AV)}	50 Hz half cycle sine wave, Conduction angle (α) = 180°, continuous operation, T _C = 86°C		10.0	А
RMS On-State Current	I _{T(RMS)}			15.7	А
Surge On-State Current		f = 60 Hz	_	176	А
	I _{TSM}	f = 50 Hz	Half cycle sine wave, single, non-repetitive	160	А
I2t Value for Fusing	I ² t	Value for 50 Hz half cycle sine wave, 1 cycle, I _{TSM} = 160 A		128	A ² •s
Critical Rising Rate of On-State Current	di/dt	$I_T = I_{T(RMS)} \times \pi$, $V_D = V_{DRM} \times 0.5$, $f \le 60$ Hz, $t_{gw} \ge 10$ μ s, $t_{gr} \le 250$ ns, $i_{gp} \ge 30$ mA (refer to Gate Trigger Circuit diagram)		50	A/µs
Peak Forward Gate Current	I _{FGM}	f ≥ 50 Hz, duty cycle ≤ 10%		2.0	Α
Peak Forward Gate Voltage	V_{FGM}	f ≥ 50 Hz, duty cycle ≤ 10%		10	V
Peak Reverse Gate Current	V_{RGM}	f ≥ 50 Hz		5.0	V
Peak Gate Power Dissipation	P _{GM}	f ≥ 50 Hz, duty cycle ≤ 10%		5.0	W
Average Gate Power Dissipation	P _{GM(AV)}	$T_J < T_J(max)$		0.5	W
Junction Temperature	TJ			-40 to 150	°C
Storage Temperature	T _{stg}	, ,		-40 to 150	°C

Thermal Characteristics May require derating at maximum conditions

Characteristic	Symbol	Test Conditions	Value	Units
Package Thermal Resistance (Junction to Case)	$R_{ heta JC}$	For AC	3.4	°C/W

Pin-out Diagram





Terminal List Table

Number	Name	Function
1	K	Cathode terminal
2	Α	Anode terminal
3	G	Gate control

All performance characteristics given are typical values for circuit or system baseline design only and are at the nominal operating voltage and an ambient temperature, TA, of 25°C, unless otherwise stated.



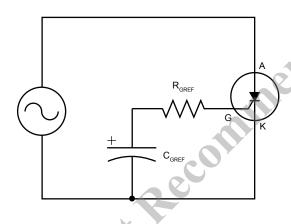


Reverse Blocking Triode Thyristor

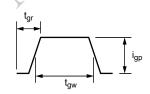
ELECTRICAL CHARACTERISTICS

Characteristics	Symbol	Test Conditions	Min.	Тур.	Max.	Unit
Off-State Leakage Current	I _{DRM}	$V_D = V_{DRM}$, $T_J = 150$ °C, $R_{GREF} = 1 \text{ k}\Omega$	_	_	2.0	mA
Reverse Leakage Current	I _{RRM}	$V_D = V_{DRM}$, $T_J = 150$ °C, $R_{GREF} = 1 \text{ k}\Omega$	_	_	2.0	mA
On-State Voltage	V _{TM}	I _{TM} = 20 A, T _C = 25°C	_	_	1.35	V
Gate Trigger Voltage	V _{GT}	$V_D = 6 \text{ V}, R_L = 10 \Omega, T_C = 25^{\circ}\text{C}$	_	0	1.0	V
Gate Trigger Current	I _{GT}	$V_D = 6 \text{ V}, R_L = 10 \Omega, T_C = 25^{\circ}\text{C}$	_	7	15	mA
Gate Non-trigger Voltage	V_{GD}	$V_D = V_{DRM} \times 0.5$, $R_{GREF} = 1 \text{ k}\Omega$, $T_J = 125^{\circ}\text{C}$	0.2	-0	_	V
Holding Current	I _H	R_{GREF} = 1 k Ω , T_J = 25°C	- 0	20	_	mA
Critical Rising Rate of Off-State Voltage	dv/dt	V_D = $V_{DRM} \times 0.5$, T_J = 125°C, R_{GREF} = 1 k Ω , C_{GREF} = 0.033 μ F	3	300	_	V/µs

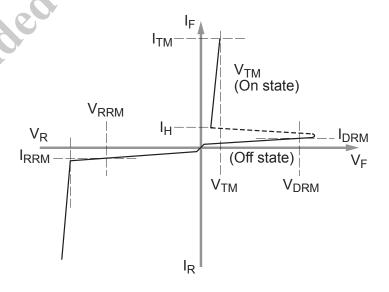
Test Circuit 1



Gate Trigger Current

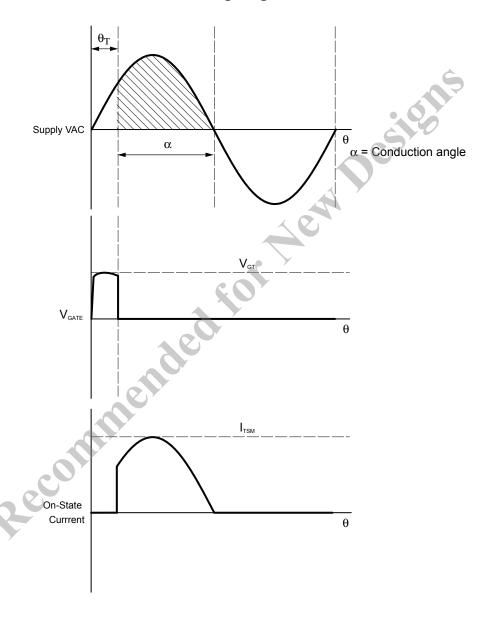


Voltage-Current Characteristic





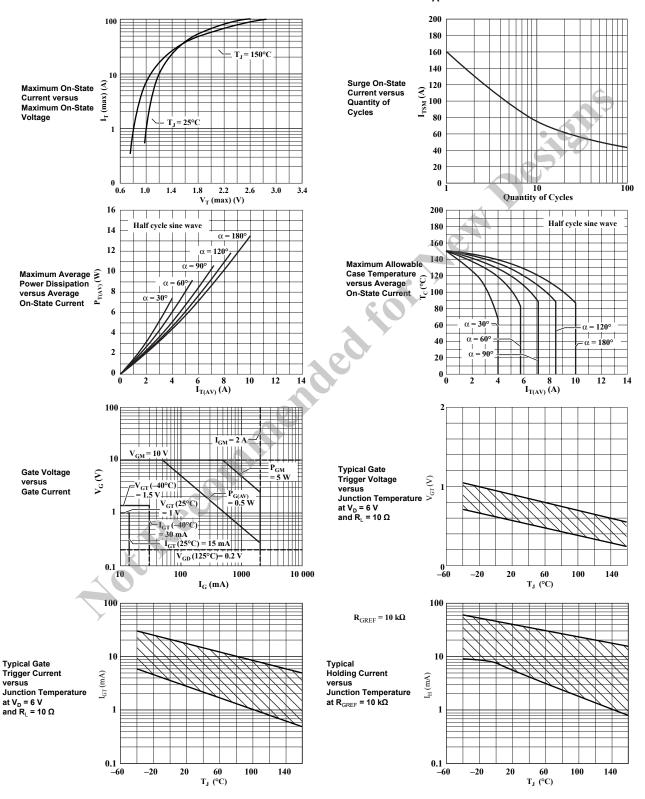
Commutation Timing Diagrams







Performance Characteristics at T_A = 25°C





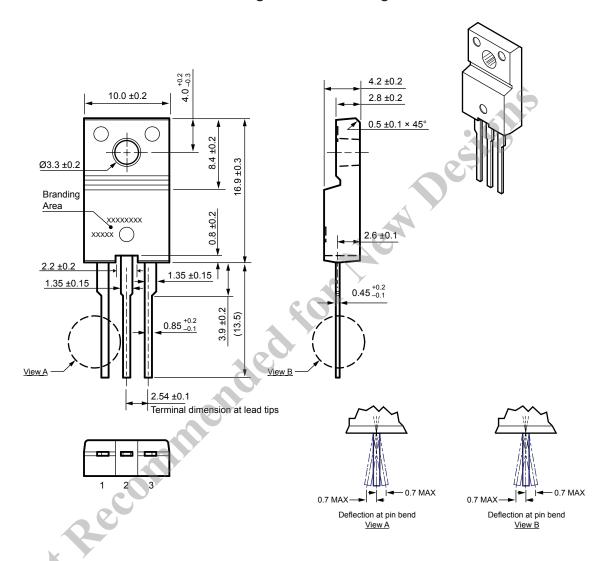


Transient Thermal Impedence versus Voltage Pulse Duration $_{\mbox{\scriptsize For AC}}$





TO-220F Package Outline Drawing



Gate burr: 0.3 mm (max.), mold flash may appear at opposite side

Terminal core material: Cu

Terminal treatment: Ni plating and Pb-free solder dip

Leadform: 600

Package: TO-220F (FM20)

Dimensions in millimeters

Branding codes (exact appearance at manufacturer discretion):

1st line, type: FA10xx 2nd line, lot: *YM*

Where: Y is the last digit of the year of manufacture

M is the month (1 to 9, O, N, D)



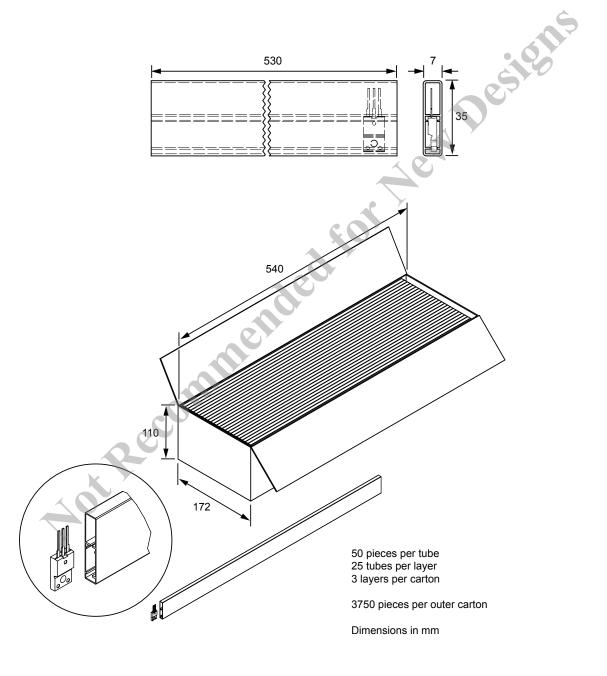
Leadframe plating Pb-free. Device meets RoHS requirements.





Packing Specification

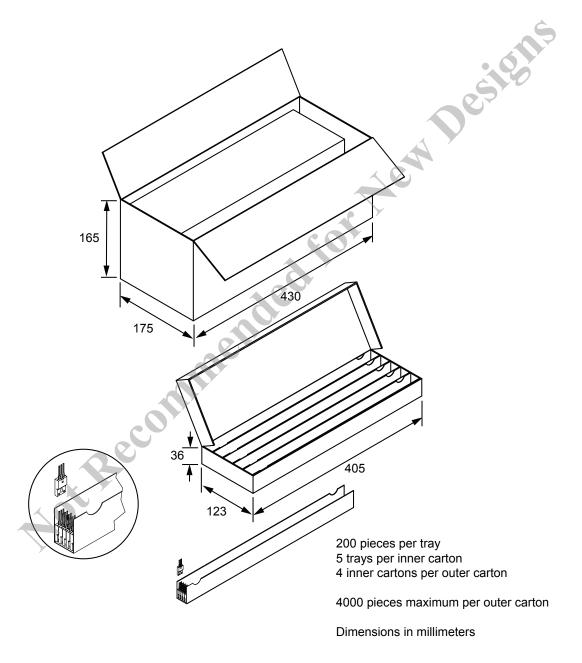
Tube Packing







Bulk Packing







Reverse Blocking Triode Thyristor



WARNING — These devices are designed to be operated at lethal voltages and energy levels. Circuit designs that embody these components must conform with applicable safety requirements. Precautions must be taken to prevent accidental contact with power-line potentials. Do not connect grounded test equipment.

The use of an isolation transformer is recommended during circuit development and breadboarding.

Because reliability can be affected adversely by improper storage environments and handling methods, please observe the following cautions.

Cautions for Storage

- Ensure that storage conditions comply with the standard temperature (5°C to 35°C) and the standard relative humidity (around 40 to 75%); avoid storage locations that experience extreme changes in temperature or humidity.
- Avoid locations where dust or harmful gases are present and avoid direct sunlight.
- Reinspect for rust on leads and solderability of products that have been stored for a long time.

Cautions for Testing and Handling

When tests are carried out during inspection testing and other standard test periods, protect the products from power surges from the testing device, shorts between adjacent products, and shorts to the heatsink.

Remarks About Using Silicone Grease with a Heatsink

- When silicone grease is used in mounting this product on a heatsink, it shall be applied evenly and thinly. If more silicone grease than required is applied, it may produce stress.
- Coat the back surface of the product and both surfaces of the insulating plate to improve heat transfer between the product and the heatsink.
- Volatile-type silicone greases may permeate the product and produce cracks after long periods of time, resulting in reduced heat radiation effect, and possibly shortening the lifetime of the product
- Our recommended silicone greases for heat radiation purposes, which will not cause any adverse effect on the product life, are indicated below:

Туре	Suppliers
G746	Shin-Etsu Chemical Co., Ltd.
YG6260	Momentive Performance Materials
SC102	Dow Corning Toray Silicone Co., Ltd.

Heatsink Mounting Method

- Torque When Tightening Mounting Screws. Thermal resistance increases when tightening torque is low, and radiation effects are decreased. When the torque is too high, the screw can strip, the heatsink can be deformed, and distortion can arise in the product frame. To avoid these problems, observe the recommended tightening torques for this product package type 0.490 to 0.686 N·m (5 to 7 kgf·cm).
- For effective heat transfer, the contact area between the product and the heatsink should be free from burrs and metal fragments, and the heatsink should be flat and large enough to contact over the entire side of the product, including mounting flange and exposed thermal pad.
- The mounting hole in customer-supplied heatsink must be less than Ø4 mm; this includes the diameter of any dimple around punched holes. This is to prevent possible deflection and cracking of the product case when fastened to the heatsink.

Soldering

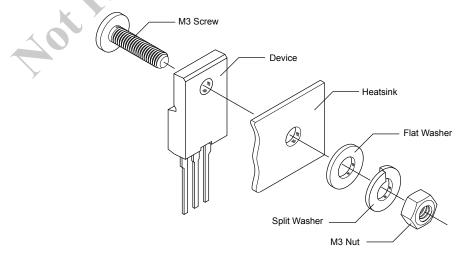
 When soldering the products, please be sure to minimize the working time, within the following limits:

260±5°C 10 s 350±5°C 3 s

 Soldering iron should be at a distance of at least 1.5 mm from the body of the products

Electrostatic Discharge

- When handling the products, operator must be grounded. Grounded wrist straps worn should have at least 1 MΩ of resistance to ground to prevent shock hazard.
- Workbenches where the products are handled should be grounded and be provided with conductive table and floor mats.
- When using measuring equipment such as a curve tracer, the equipment should be grounded.
- When soldering the products, the head of soldering irons or the solder bath must be grounded in other to prevent leak voltages generated by them from being applied to the products.
- The products should always be stored and transported in our shipping containers or conductive containers, or be wrapped in aluminum foil.







Reverse Blocking Triode Thyristor



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